Supplementary Information for Optical Properties of $In_{2x}Ga_{2-2x}O_3$ Nanowires Revealed by Photoacoustic Spectroscopy

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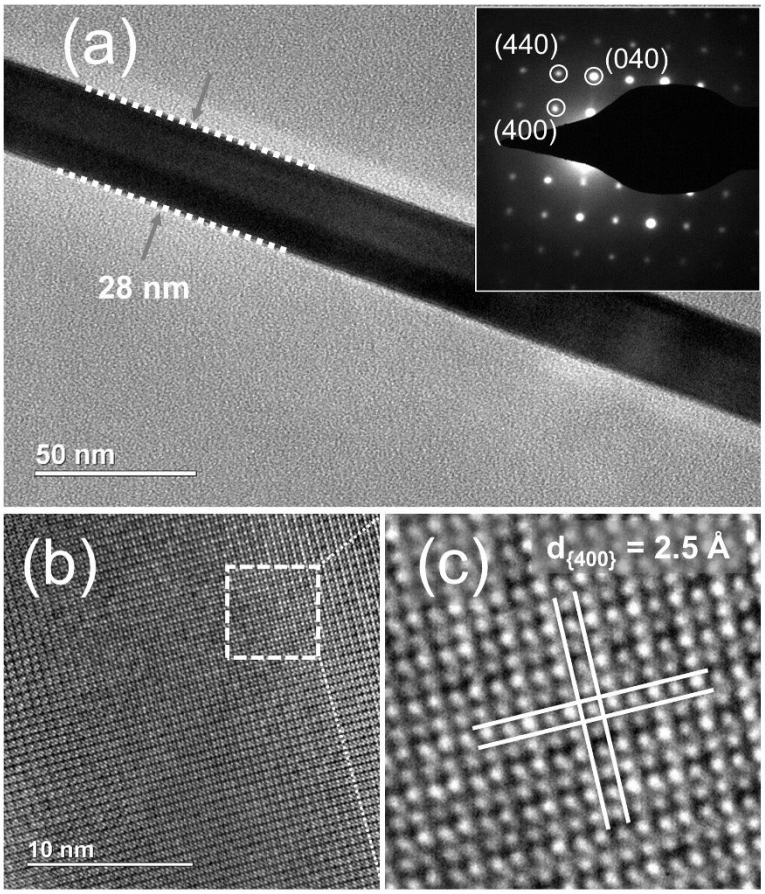

Figure S1. (a) TEM image and (inset) the corresponding SAED patterns of $In_{1.8}Ga_{0.2}O_3$ NWs. (b) and (c) HRTEM images of $In_{1.8}Ga_{0.2}O_3$ NWs.

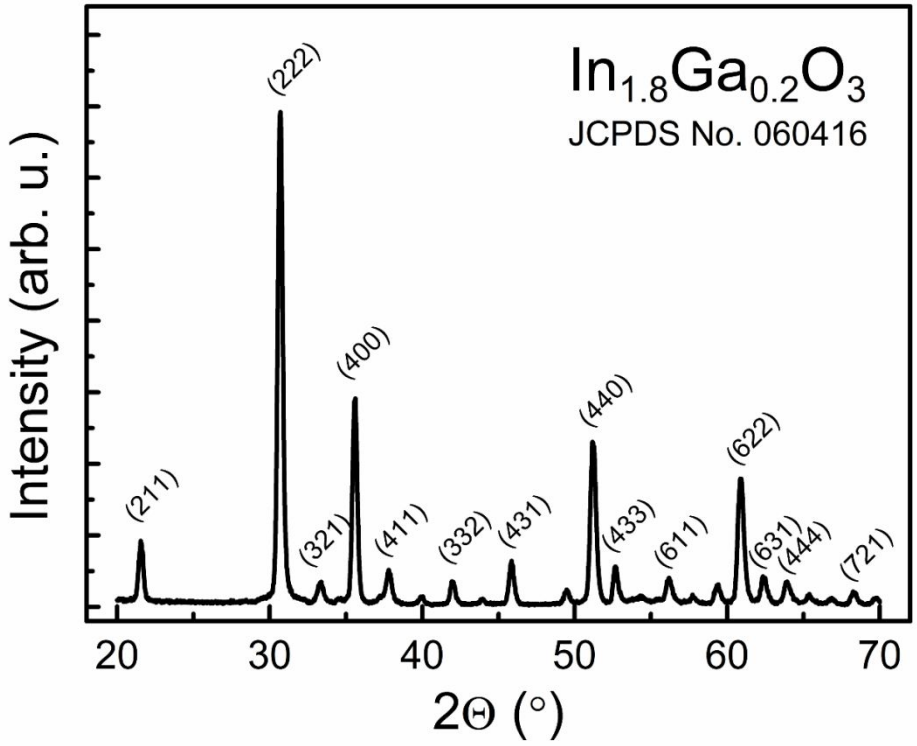

Figure S2. XRD patterns of the obtained $In_{1.8}Ga_{0.2}O_3$ NWs.

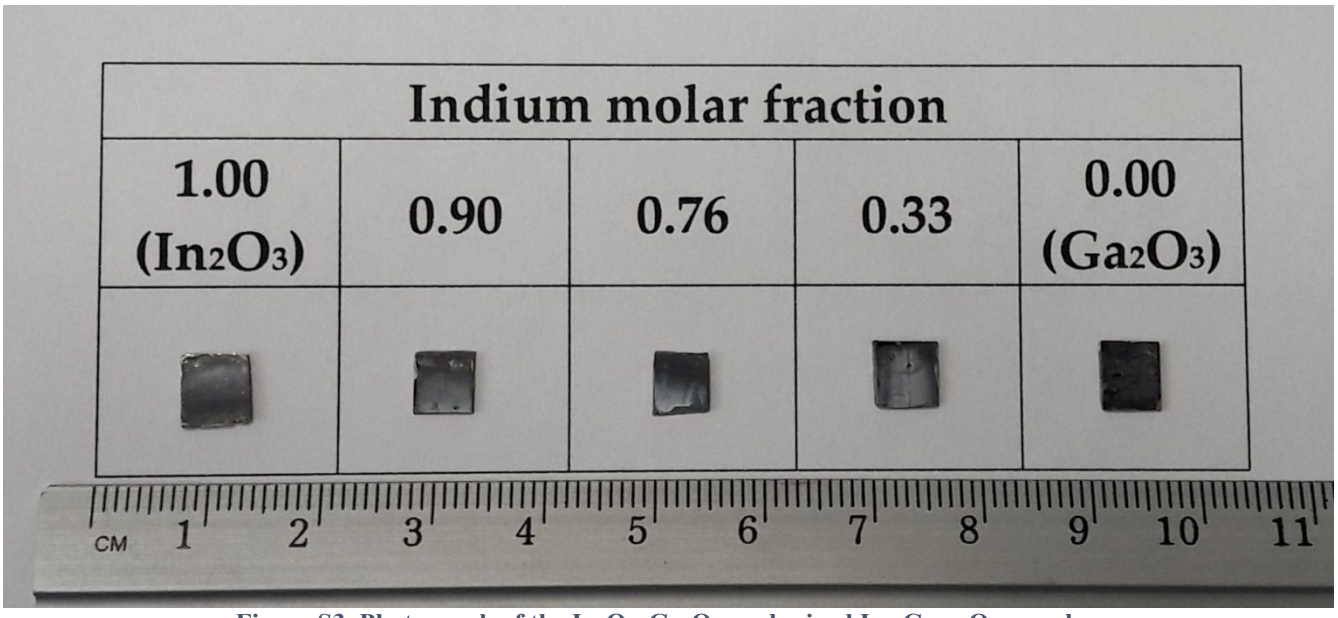

Figure S3. Photograph of the In_2O_3, Ga_2O_3, and mixed $In_{2x}Ga_{2-2x}O_3$ samples.

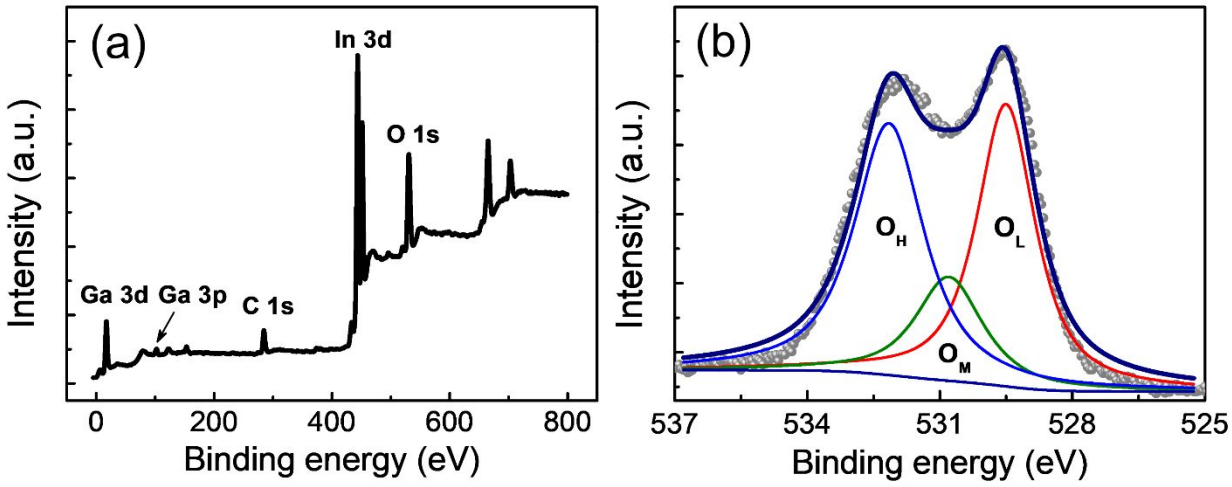

Figure S4. (a) XPS wide scans and (b) O 1s peak analysis of $In_{1.8}Ga_{0.2}O_3$ NWs.